

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments
1	BRS	L1	14624	(tantalum) near40 (tungsten) near15 (molybdenum)	USPA T; US-P GPUB ; EPO; JPO; DERW ENT; IBM TDB	2004/01/2 4 13:53	
2	BRS	L2	9089	(tantalum) near30 (metal\$3) near40 (tungsten) near15 (molybdenum)	USPA T; US-P GPUB ; EPO; JPO; DERW ENT; IBM TDB	2004/01/2 4 13:54	
3	BRS	L3	23568	(tantalum) near30 (metal\$3) near40 (tungsten) nnear15 (weight) near15 (molybdenum)	USPA T; US-P GPUB ; EPO; JPO; DERW ENT; IBM TDB	2004/01/2 4 13:54	
4	BRS	L5	23568	(tantalum) near30 (metal\$3) near40 (tungsten) nnear15 (weight) near15 (molybdenum)	USPA T; US-P GPUB ; EPO; JPO; DERW ENT; IBM TDB	2004/01/2 4 13:55	

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments
5	BRS	L6	10152	(tantalum) near30 (metal\$3 near5 impurit\$3) near40 (tungsten) nnear15 (weight) near15 (molybdenum)	USPAT; US-P GPUB; ; EPO; JPO; DERW ENT; IBM TDB	2004/01/2 4 13:56	
6	BRS	L7	10103	(purity near3 tantalum) near30 (metal\$3 near5 impurit\$3) near40 (tungsten) nnear15 (weight) near15 (molybdenum)	USPAT; US-P GPUB; ; EPO; JPO; DERW ENT; IBM TDB	2004/01/2 4 13:56	
7	BRS	L8	10103	(high near1 purity near3 tantalum) near30 (metal\$3 near5 impurit\$3) near40 (tungsten) nnear15 (weight) near15 (molybdenum)	USPAT; US-P GPUB; ; EPO; JPO; DERW ENT; IBM TDB	2004/01/2 4 13:59	
8	BRS	L9	10103	(high near1 purity near tantalum) near30 (metal\$3 near5 impurit\$3) near40 (tungsten) nnear15 (weight) near15 (molybdenum)	USPAT; US-P GPUB; ; EPO; JPO; DERW ENT; IBM TDB	2004/01/2 4 13:59	

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments
9	BRS	L11	2	(high near1 purity near5 tantalum) near30 (metal\$3 near5 impurit\$3) near20 (tungsten) near15 (weight) near15 (molybdenum)	USPA T; US-P GPUB ; EPO; JPO; DERW ENT; IBM TDB	2004/01/2 4 13:59	
10	BRS	L12	2	(high near1 purity near5 tantalum) near30 (metal\$3 near5 impurit\$3) near40 (tungsten) near15 (weight) near15 (molybdenum)	USPA T; US-P GPUB ; EPO; JPO; DERW ENT; IBM TDB	2004/01/2 4 14:00	
11	BRS	L13	6	5244556.pn. or 3984208.pn. or 5972288.pn.	USPA T; US-P GPUB ; EPO; JPO; DERW ENT; IBM TDB	2004/01/2 4 14:01	
12	BRS	L10	2	(high near1 purity near tantalum) near30 (metal\$3 near5 impurit\$3) near20 (tungsten) near15 (weight) near15 (molybdenum)	USPA T; US-P GPUB ; EPO; JPO; DERW ENT; IBM TDB	2004/01/2 4 14:04	

	U	1	PT	P	Document ID	Issue Date	Pages	Title
1	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	US 6566161 B1	20030520	13	Tantalum sputtering target and method of manufacture
2	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	US 6323055 B	20020921	12	Highly pure tantalum preparation method for use in manufacture of electronic capacitors, bulk capacitors, thin film capacitors